

Digital Transistors (BRT) R1 = 10 k Ω , R2 = 10 k Ω

NPN Transistors with Monolithic Bias Resistor Network

MUN2211, MMUN2211L, MUN5211, DTC114EE, DTC114EM3, NSBC114EF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

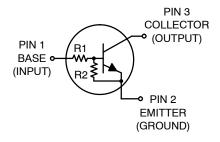
MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

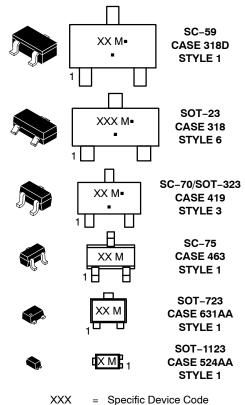
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

PIN CONNECTIONS



MARKING DIAGRAMS



M = Date Code*
■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2211T1G, SMUN2211T1G	8A	SC-59 (Pb-Free)	3000 / Tape & Reel
MUN2211T3G, SMUN2211T3G	8A	SC-59 (Pb-Free)	10000 / Tape & Reel
MMUN2211LT1G, SMMUN2211LT1G	A8A	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMUN2211LT3G, SMMUN2211LT3G	A8A	SOT-23 (Pb-Free)	10000 / Tape & Reel
MUN5211T1G, SMUN5211T1G	8A	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
SMUN5211T3G	8A	SC-70/SOT-323 (Pb-Free)	10000 / Tape & Reel
DTC114EET1G, SDTC114EET1G	8A	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC114EM3T5G	8A	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC114EF3T5G	А	SOT-1123 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

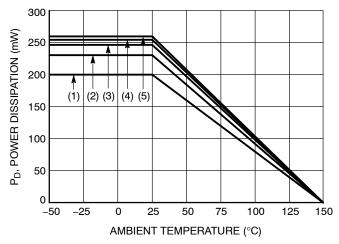


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Table 2. THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTI	CS (SC-59) (MUN2211)			
Total Device Dissipation T _A = 25°C (Note 1) (Note 2)		P _D	230 338	mW
Derate above 25°C (Note 2)	(Note 1)		1.8 2.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	540 370	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SOT-23) (MMUN2211L)			
Total Device Dissipation T _A = 25°C (Note 1)		P _D	246	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		400 2.0 3.2	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temper	rature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SC-70/SOT-323) (MUN5211)			
Total Device Dissipation T _A = 25°C (Note 1)		P _D	202	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		310 1.6 2.5	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SC-75) (DTC114EE)			
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$		P _D	200	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		300 1.6 2.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temper	rature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTIC	CS (SOT-723) (DTC114EM3)	-	-	
Total Device Dissipation T _A = 25°C (Note 1)		P _D	260	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		600 2.0 4.8	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	480 205	°C/W
Junction and Storage Temper	rature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBC114EF3)			
Total Device Dissipation T _A = 25°C (Note 3) (Note 4) Derate above 25°C (Note 3) (Note 4)	P _D	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, (Note 3) Junction to Ambient (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead (Note 3)	$R_{ heta JL}$	193	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. FLECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector–Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	I _{CBO}	_	_	100	nAdc
Collector–Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	_	_	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	_	-	0.5	mAdc
Collector–Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _(BR) CBO	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I _C = 2.0 mA, I _B = 0)	V _(BR) CEO	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	35	60	-	
Collector–Emitter Saturation Voltage (Note 5) (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}	_	-	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A})$	$V_{i(off)}$	-	1.2	0.8	Vdc
Input Voltage (on) (V _{CE} = 0.3 V, I _C = 10 mA)	V _{i(on)}	2.5	1.8	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0 \text{ V}$, $V_B = 2.5 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R ₁ /R ₂	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 5. Pulsed Condition: Pulse Width = 300 μ sec, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS MUN2211, MMUN2211L, MUN5211, DTC114EE, DTC114EM3

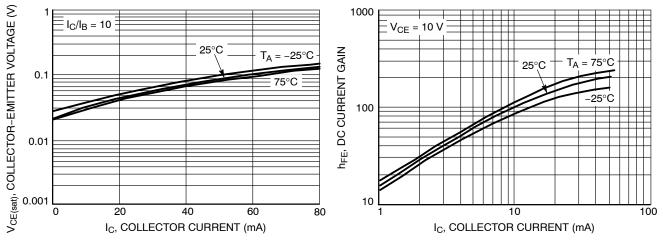


Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain

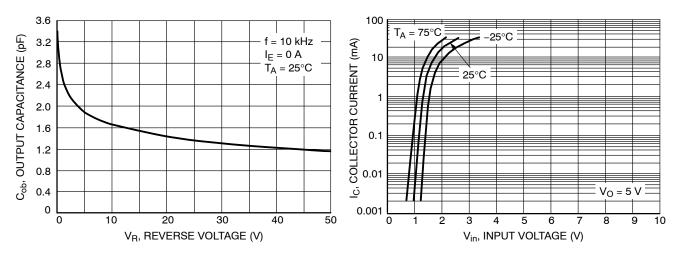


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

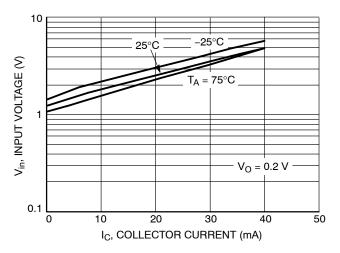
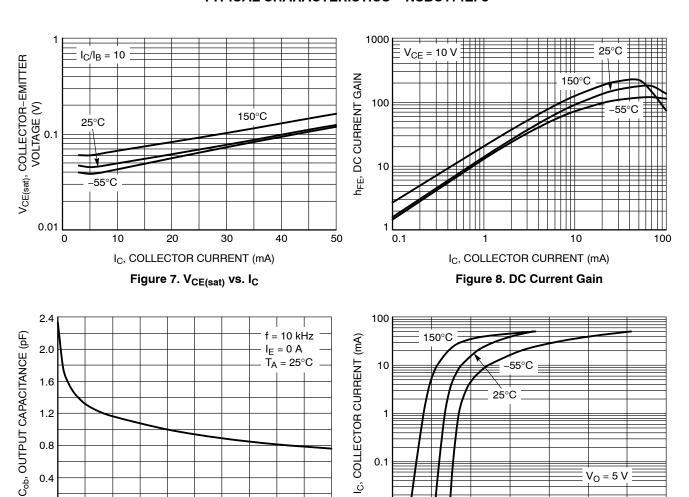


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS - NSBC114EF3



V_R, REVERSE VOLTAGE (V) Figure 9. Output Capacitance

30

40

20

10

0

0

V_{in}, INPUT VOLTAGE (V) Figure 10. Output Current vs. Input Voltage

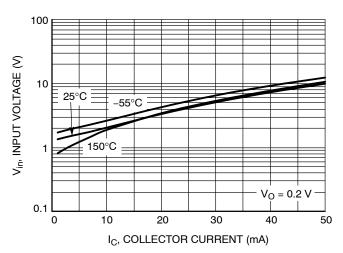
4

3

 $V_0 = 5 V$

6

5



50

0.01

0

Figure 11. Input Voltage vs. Output Current



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

3. CATHODE



SCALE 2:1

SC-59 CASE 318D-04 ISSUE H

DATE 28 JUN 2012

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

GENERIC MARKING DIAGRAM



XXX = Specific Device Code

Μ = Date Code = Pb-Free Package*

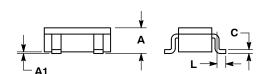
(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

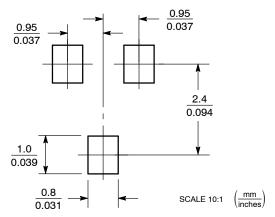


STYLE 4:		STYLE 5:		STYLE 6	:
PIN 1. C	CATHODE	PIN 1.	CATHODE	PIN 1	ANODE
2. N	I.C.	2.	CATHODE	2	CATHODE
3. A	NODE	3.	ANODE	3	ANODE/CATHODE

Ε ΗE



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB42664B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-59	•	PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.





SC-70 (SOT-323) CASE 419 ISSUE P

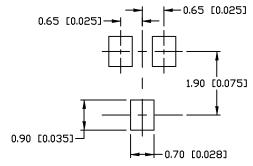
END VIEW

DATE 07 OCT 2021

NOTES:

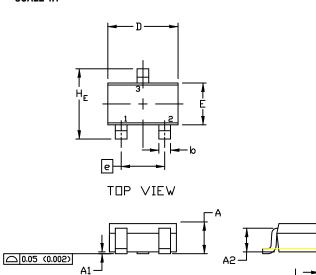
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	С
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095
e e1 L	1.20	1.30 0.65 BSC 0.38	1.40	0.047	0.051 0.026 BS 0.015	0.05 C 0.02



For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM

SIDE VIEW



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE





SC-75/SOT-416 CASE 463-01 **ISSUE G**

DATE 07 AUG 2015





STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

-		MILLIMETERS			INCHES		
L	DIM	MIN	NOM	MAX	MIN	NOM	MAX
	Α	0.70	0.80	0.90	0.027	0.031	0.035
L	A1	0.00	0.05	0.10	0.000	0.002	0.004
	b	0.15	0.20	0.30	0.006	0.008	0.012
	С	0.10	0.15	0.25	0.004	0.006	0.010
	D	1.55	1.60	1.65	0.061	0.063	0.065
	Е	0.70	0.80	0.90	0.027	0.031	0.035
	е	1.00 BSC			0.04 BSC)	
	L	0.10	0.15	0.20	0.004	0.006	0.008
	HE	1.50	1.60	1.70	0.060	0.063	0.067

GENERIC MARKING DIAGRAM*



XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

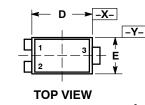




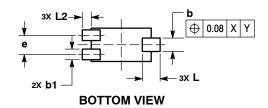
SOT-1123 CASE 524AA ISSUE C

DATE 29 NOV 2011

SCALE 8:1







SOLDERING FOOTPRINT*



STVI F 2

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN MAX			
Α	0.34	0.40		
b	0.15	0.28		
b1	0.10	0.20		
c	0.07	0.17		
D	0.75	0.85		
Е	0.55	0.65		
Φ	0.35	0.40		
HE	0.95	1.05		
L	0.185 REF			
L2	0.05	0.15		

GENERIC MARKING DIAGRAM*



= Specific Device Code Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
EMITTER	2. N/C	2. ANODE	CATHODE	SOURCE
COLLECTOR	CATHODE	CATHODE	ANODE	DRAIN

STVLE 3

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P		PAGE 1 OF 1	

STVLE 5

STVLE 4:

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

STVI F 1:



SOT-723 CASE 631AA-01 ISSUE D

DATE 10 AUG 2009

NOTES:

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			
DIM	MIN NOM MAX			
Α	0.45	0.50	0.55	
b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
E	0.75	0.80	0.85	
е	0.40 BSC			
ΗE	1.15	1.20	1.25	
L	0.29 REF			
L2	0.15	0.20	0.25	

GENERIC MARKING DIAGRAM*

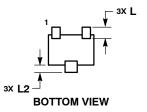


= Specific Device Code XX Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

-X-2X b ⊕ 0.08 X Y **TOP VIEW**

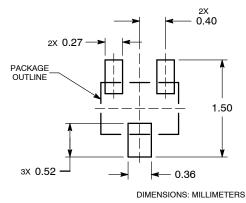




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-723		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

<u>MUN2211T1 MUN2211T1G MUN2211T3 MUN2211T3G MUN5211T1 MMUN2211LT1 MMUN2211LT1G MMUN2211LT3G DTC114EET1 DTC114EET1G DTC114EM3T5G MUN2211JT1G MUN5211T1G NSBC114EF3T5G SMMUN2211LT1G SDTC114EET1G SMUN5211T1G SMMUN2211LT3G SMUN5211T3G SMUN2211T3G SMUN2</u>